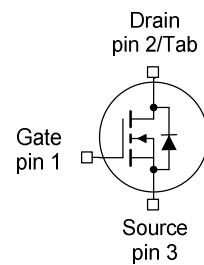


OptiMOS[®] -T2 Power-Transistor

Product Summary

V_{DS}	30	V
$R_{DS(on),max}$	5.5	m Ω
I_D	50	A

- N-channel - Enhancement mode
- Automotive AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green product (RoHS compliant)
- 100% Avalanche tested

PG-TO252-3-11


Type	Package	Marking
IPD50N03S4L-06	PG-TO252-3-11	4N03L06

Maximum ratings, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current ¹⁾	I_D	$T_C=25^\circ\text{C}$, $V_{GS}=10\text{V}$	50	A
		$T_C=100^\circ\text{C}$, $V_{GS}=10\text{V}^{2)}$	50	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25^\circ\text{C}$	200	
Avalanche energy, single pulse ²⁾	E_{AS}	$I_D=50\text{A}$	36	mJ
Avalanche current, single pulse	I_{AS}	-	50	A
Gate source voltage	V_{GS}	-	± 16	V
Power dissipation	P_{tot}	$T_C=25^\circ\text{C}$	56	W
Operating and storage temperature	T_j, T_{stg}	-	-55 ... +175	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1	-	-	55/175/56	-

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	-	-	-	2.7	K/W
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm ² cooling area ³⁾	-	-	40	

Electrical characteristics, at $T_j=25^\circ\text{C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=1\text{mA}$	30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=20\mu\text{A}$	1.0	1.5	2.2	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V, T_j=25^\circ\text{C}$	-	0.1	1	μA
		$V_{DS}=30V, V_{GS}=0V, T_j=125^\circ\text{C}^{2)}$	-	10	100	
Gate-source leakage current	I_{GSS}	$V_{GS}=16V, V_{DS}=0V$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=25\text{A}$	-	6.9	9.0	m Ω
		$V_{GS}=10V, I_D=50\text{A}$	-	4.9	5.5	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=25V,$ $f=1MHz$	-	1790	2330	pF
Output capacitance	C_{oss}		-	460	600	
Reverse transfer capacitance	C_{rss}		-	17	34	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=15V, V_{GS}=10V,$ $I_D=30A, R_G=1.6\Omega$	-	3	-	ns
Rise time	t_r		-	1	-	
Turn-off delay time	$t_{d(off)}$		-	19	-	
Fall time	t_f		-	7	-	

Gate Charge Characteristics²⁾

Gate to source charge	Q_{gs}	$V_{DD}=24V, I_D=50A,$ $V_{GS}=0$ to 10V	-	6	8	nC
Gate to drain charge	Q_{gd}		-	3	6	
Gate charge total	Q_g		-	24	31	
Gate plateau voltage	$V_{plateau}$		-	3.2	-	V

Reverse Diode

Diode continuous forward current ²⁾	I_S	$T_C=25^\circ C$	-	-	50	A
Diode pulse current ²⁾	$I_{S,pulse}$		-	-	200	
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_F=50A,$ $T_J=25^\circ C$	0.6	0.95	1.3	V
Reverse recovery time ²⁾	t_{rr}	$V_R=30V, I_F=I_S,$ $di_F/dt=100A/\mu s$	-	17	-	ns
Reverse recovery charge ²⁾	Q_{rr}		-	14	-	nC

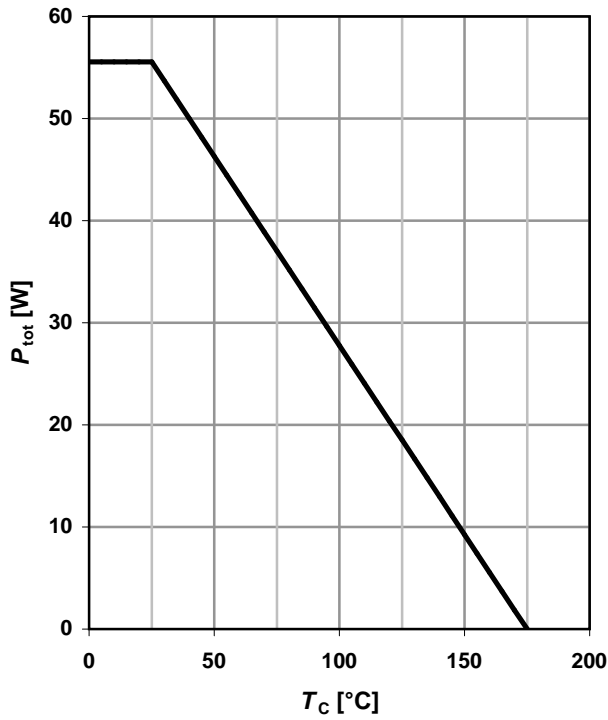
¹⁾ Current is limited by bondwire; with an $R_{thJC} = 2.7K/W$ the chip is able to carry 77A at 25°C.

²⁾ Defined by design. Not subject to production test.

³⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

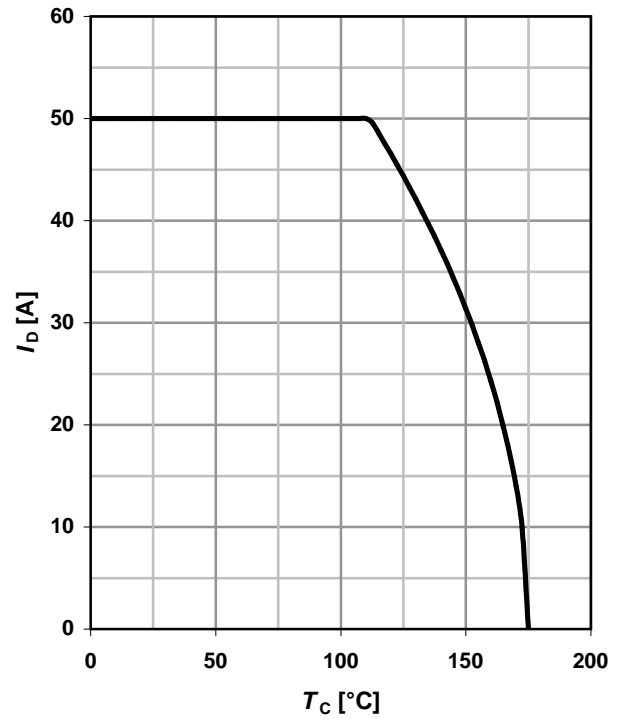
1 Power dissipation

$P_{tot} = f(T_C); V_{GS} \geq 6 V$



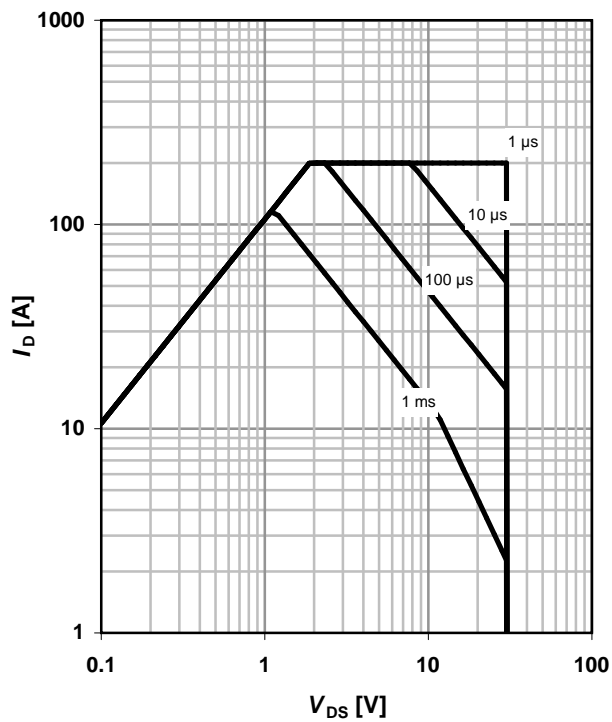
2 Drain current

$I_D = f(T_C); V_{GS} \geq 6 V$



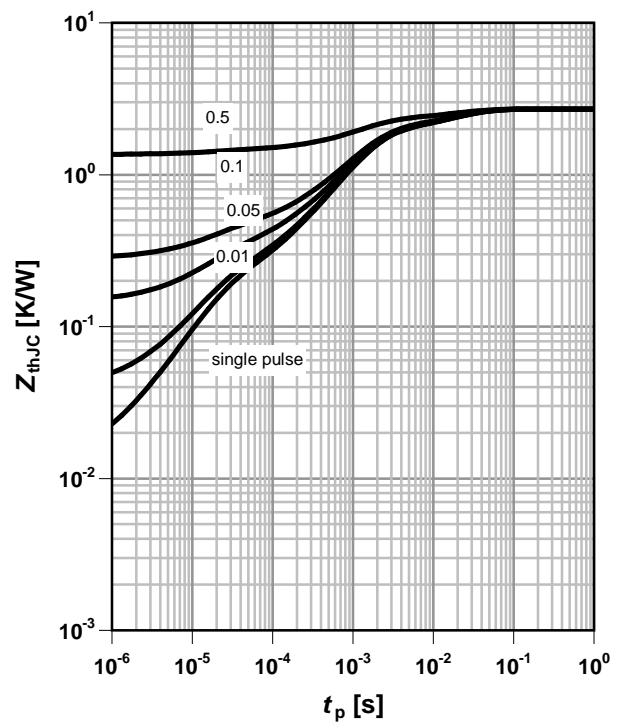
$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$

parameter: t_p



$Z_{thJC} = f(t_p)$

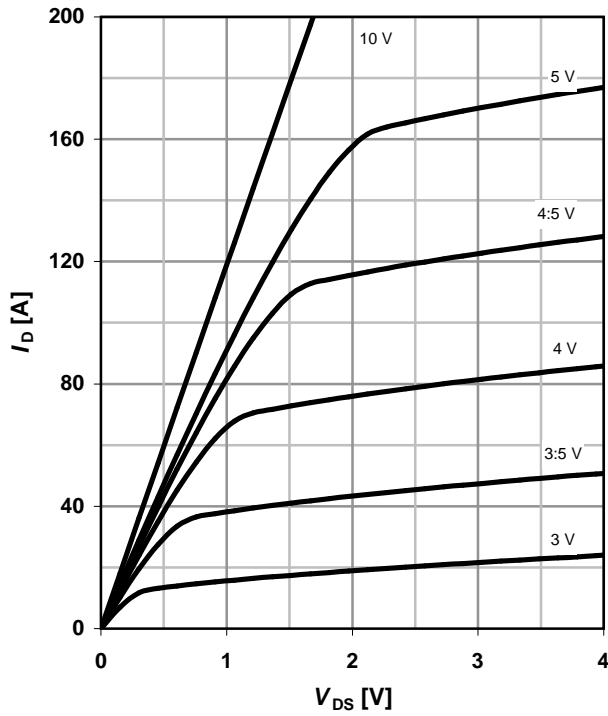
parameter: $D = t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

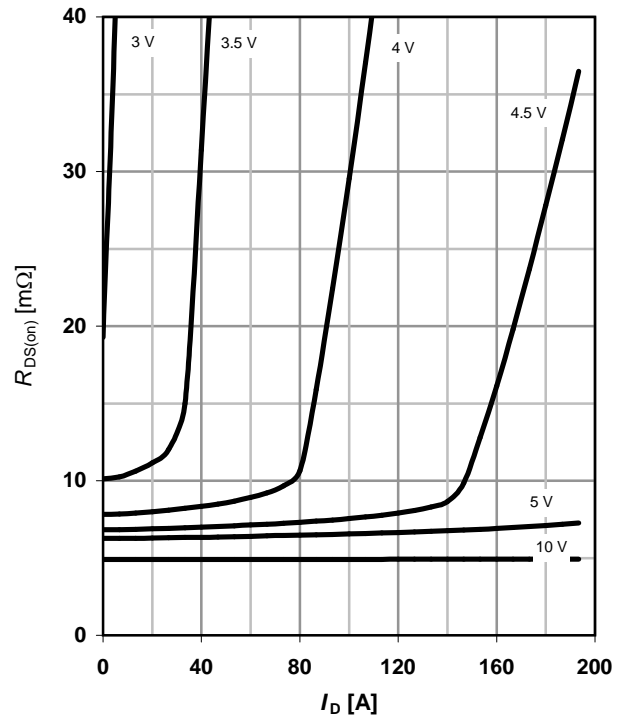
parameter: V_{GS}



6 Typ. drain-source on-state resistance

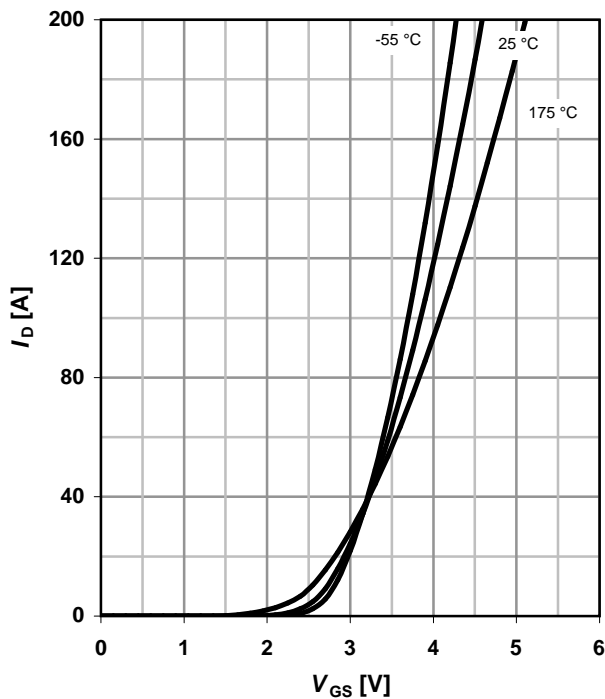
$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

parameter: V_{GS}

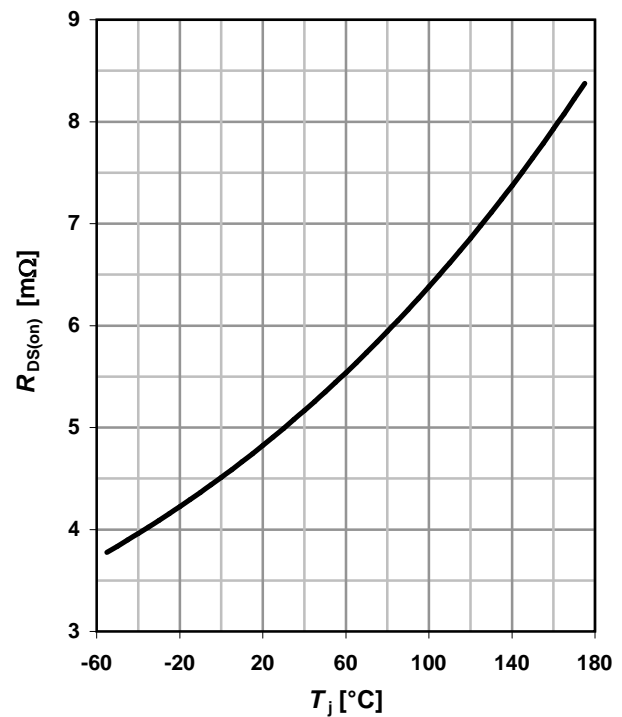


$I_D = f(V_{GS}); V_{DS} = 6\text{ V}$

parameter: T_j



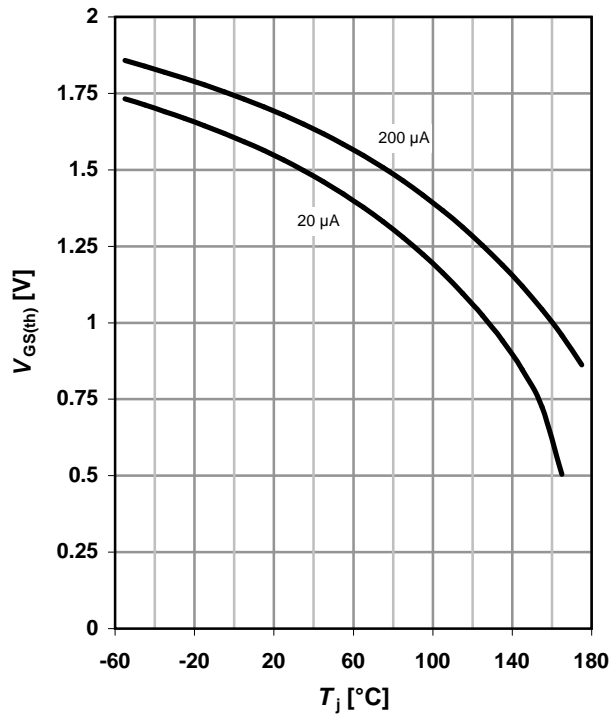
$R_{DS(on)} = f(T_j); I_D = 50\text{ A}; V_{GS} = 10\text{ V}$



9 Typ. gate threshold voltage

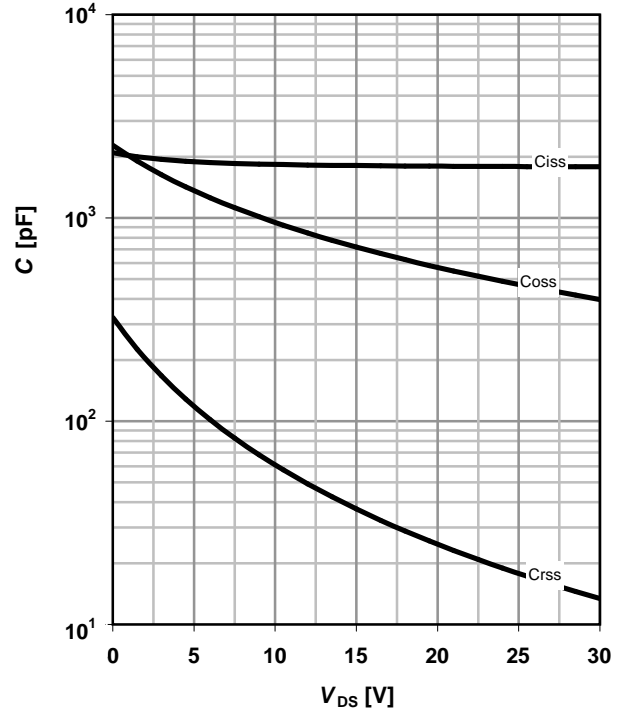
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter: I_D



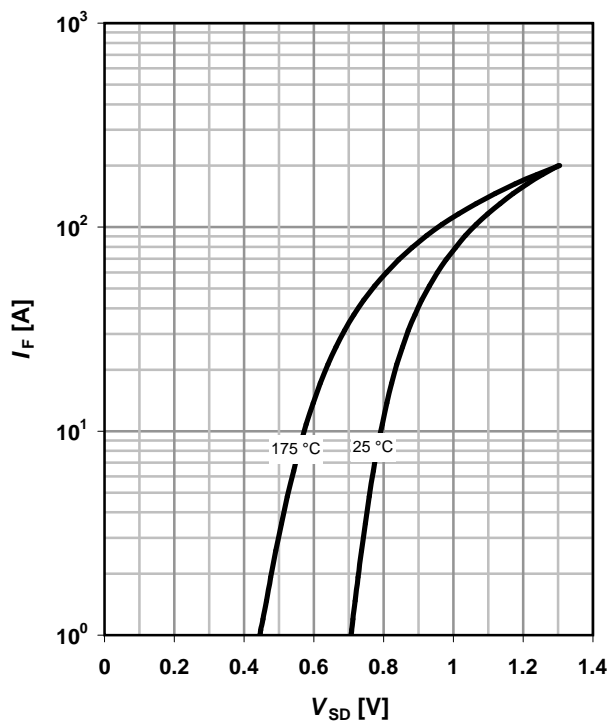
10 Typ. capacitances

$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



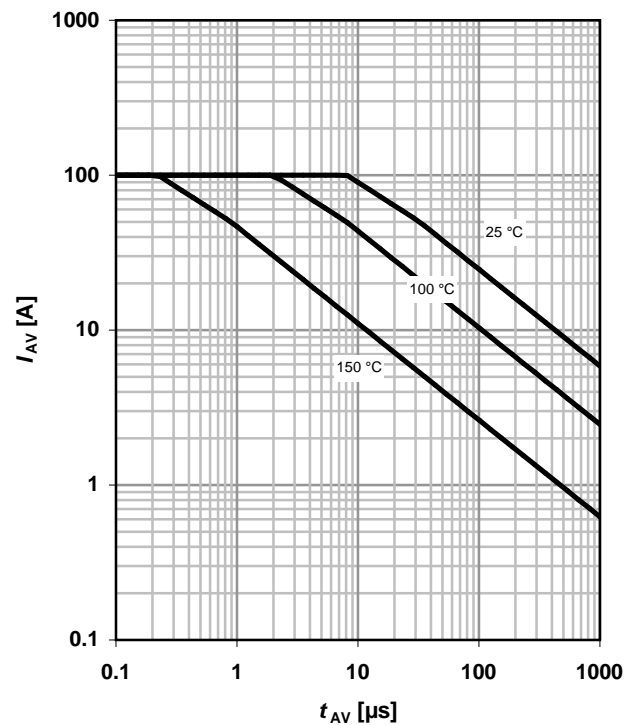
$I_F = f(V_{SD})$

parameter: T_j



$I_{AS} = f(t_{AV})$

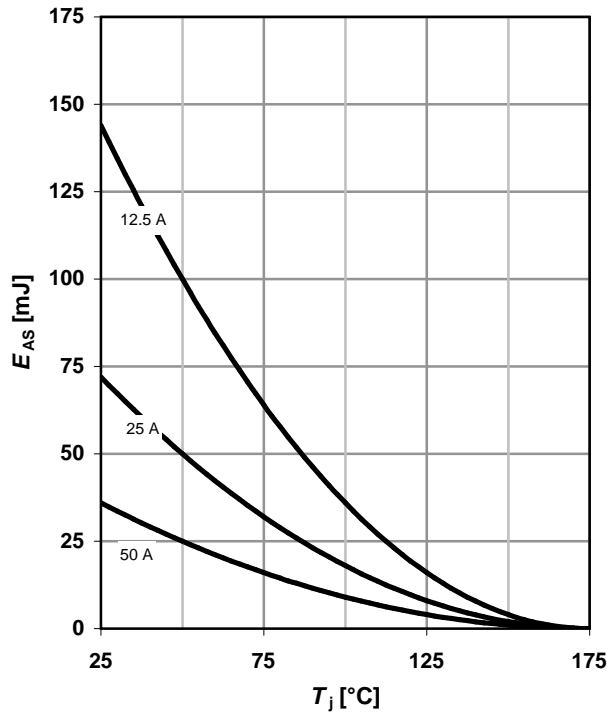
parameter: $T_{j(start)}$



13 Avalanche energy

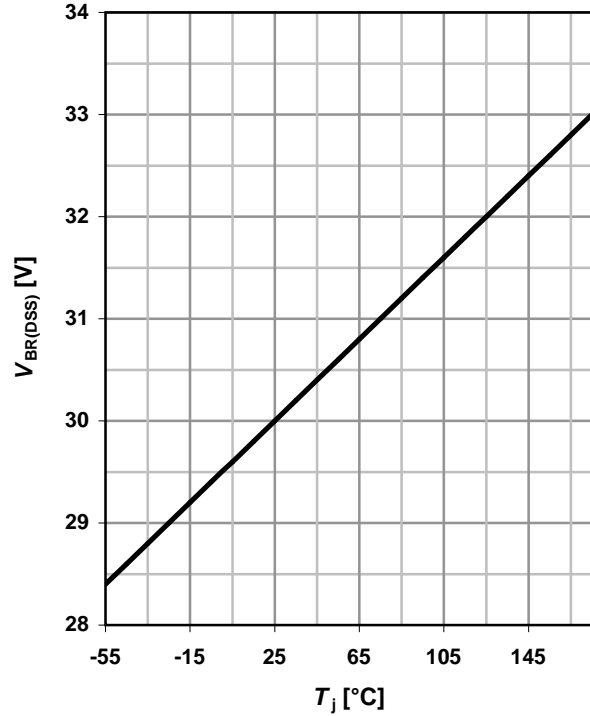
$$E_{AS} = f(T_j)$$

parameter: I_D



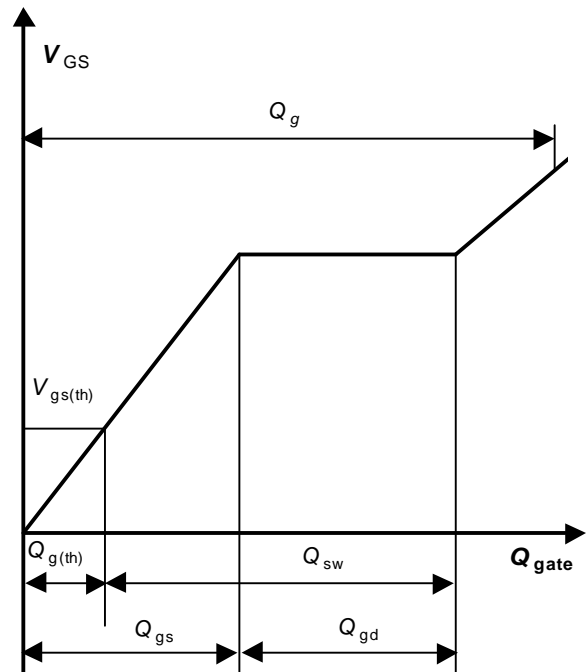
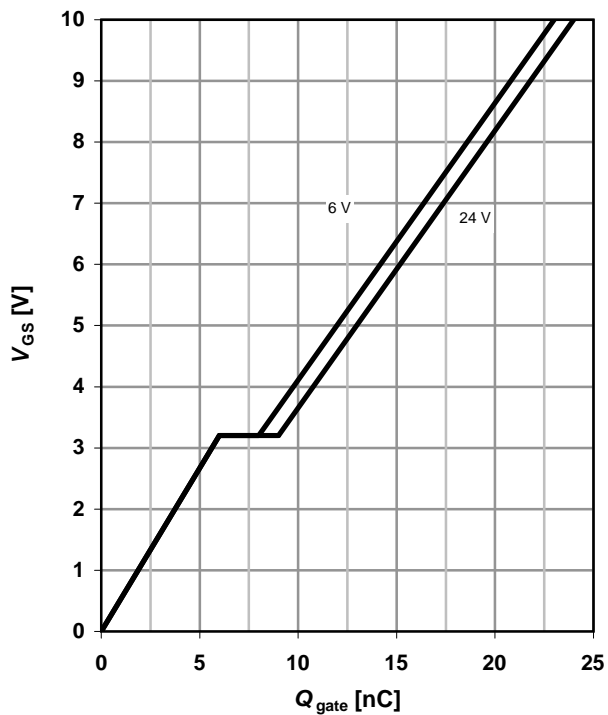
14 Drain-source breakdown voltage

$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$



$$V_{GS} = f(Q_{gate}); I_D = 50 \text{ A pulsed}$$

parameter: V_{DD}



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